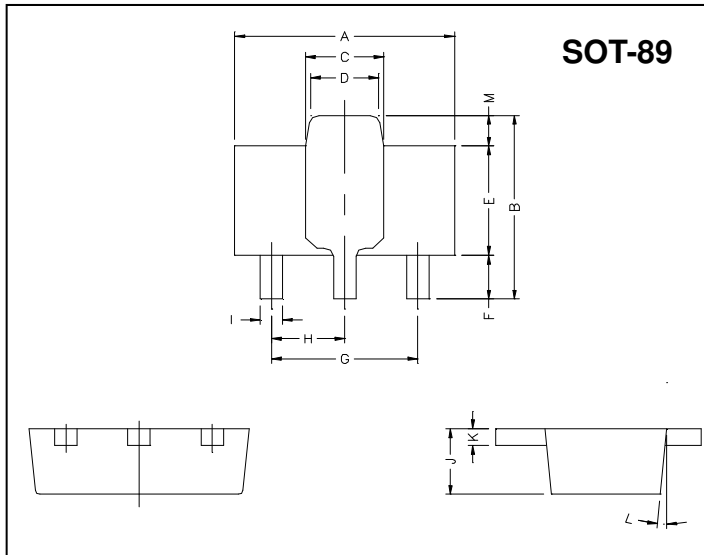
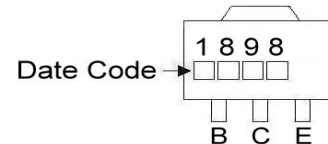


GM1898**NPN EPITAXIAL PLANAR TRANSISTOR****Description**

The GM1898 is designed for switching applications.

Package Dimensions**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5°	TYP.
			M	0.70	REF.

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	100	V
Collector to Emitter Voltage	VCEO	80	V
Emitter to Base Voltage	VEBO	5.0	V
Collector Current	IC	1	A
	ICP (Single pulse Pw=20ms)	2	A
Total Power Dissipation	PD	500	mW

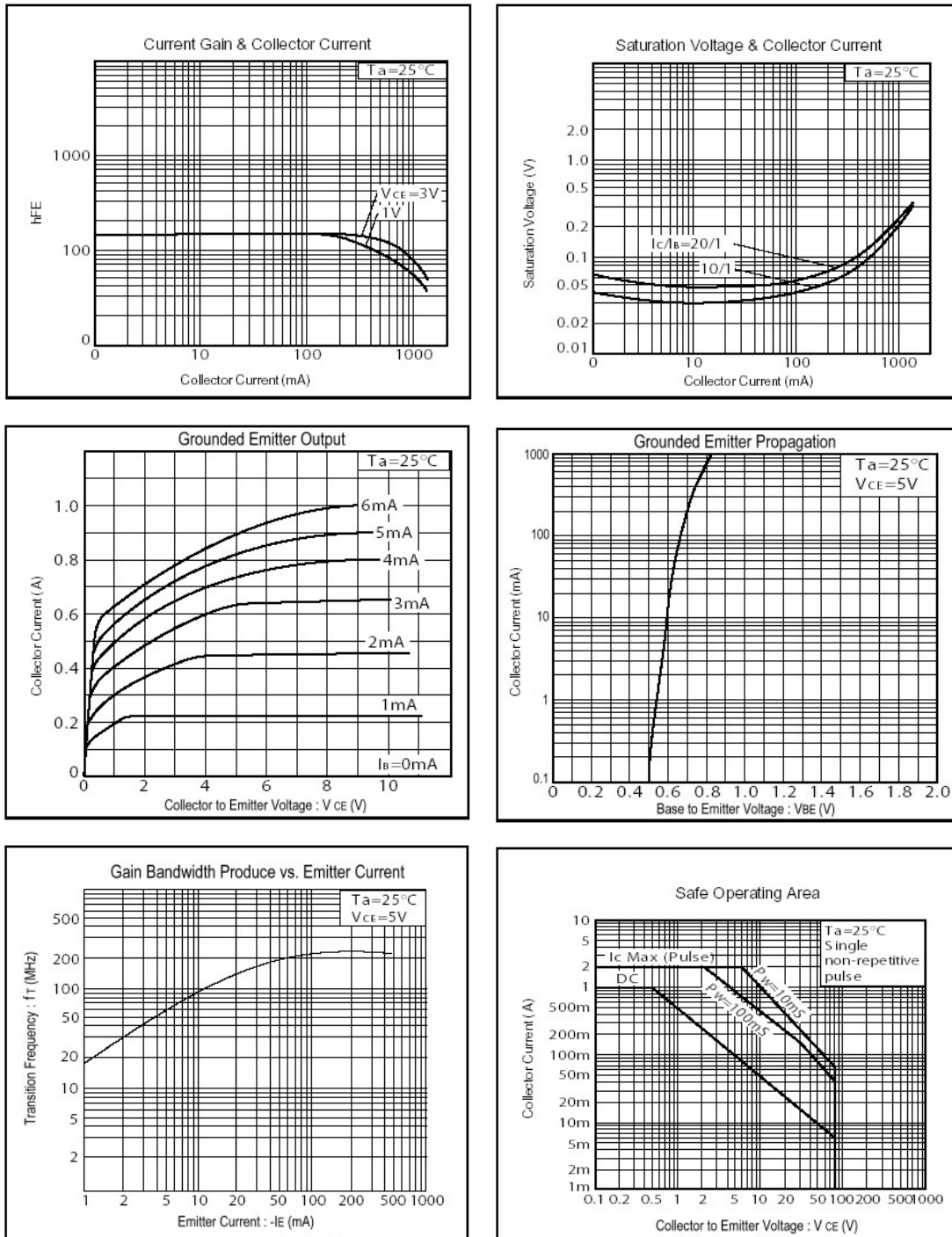
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	100	-	-	V	IC=50uA
BVCEO	80	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=50uA
ICBO	-	-	1	uA	VCB=80V
IEBO	-	-	1	uA	VEB=4V
VCE(sat)	-	-	400	mV	IC=500mA, IB=20mA
hFE	82	-	390		VCE=3V, IC=500mA
fT		100	-	MHZ	VCE=10V, IC=50mA, f=100MHZ
Cob	-	25	-	pF	VCB=10V, IE=0, f=1MHz

Classification Of hFE

Rank	P	Q	R
hFE	82-180	120-270	180-390

Characteristics Curve



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Head Office And Factory:

- Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165